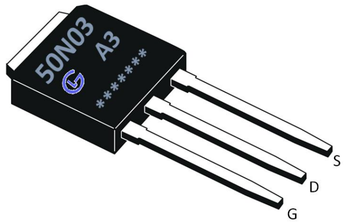
GL50N03A3

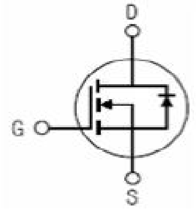
GL Silicon N-Channel Power MOSFET

V_{DSS}	30	V
I_D	50	A
P_D	60	W
$R_{DS(ON)type}$	5.8	mΩ

TO-251



Inner Equivalent Principium Chart



General Description

The GL50N03A3 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge It can be used in a wide variety of applications. The package form is TO-251, which accords with the RoHS standard.

Features

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Absolute (Tc=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	30	V
I_D	Continuous Drain Current	50	A
	Continuous Drain Current T_C = 100 °C	35	A
I_{DM}	Pulsed Drain Current	200	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS} [a2]	Single Pulse Avalanche Energy	70	mJ
E_{AR} [a1]	Avalanche Energy ,Repetitive	15	mJ
I_{AR} [a1]	Avalanche Current	30	A
dv/dt [a3]	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	60	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, −55 to 175	℃
T_L	Maximum Temperature for Soldering	300	℃

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{θJA}$	Junction-to-Ambient	2.5	℃/W

Electrical Characteristics (Tc=25℃ unless otherwise specified)

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	I_D=250uA,Reference25℃	--	0.1	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS}=30V,V_{GS}=0V,T_a=25℃	--	--	1	μA
		V_{DS}=24V,V_{GS}=0V,T_a=125℃	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+20V	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-20V	--	--	-1	μA

ON Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=25A	--	5.8	7.2	mΩ
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.0	1.4	2.0	V
Pulse width tp≤380μs,δ≤2%						

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	V_{DS}=5V,I_D=25A	15	--	--	S
C_{iss}	Input Capacitance	V_{GS}=0V,V_{DS}=15V f=1.0MHz	--	1800	--	pF
C_{oss}	Output Capacitance		--	240	--	
C_{rss}	Reverse Transfer Capacitance		--	180	--	

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D=25A,V_{DD}=15V V_{GS}=10V,R_G=3.0Ω	--	10	--	ns
t_r	Rise Time		--	9	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	30	--	
t_f	Fall Time		--	6	--	
Q_g	Total Gate Charge	I_D =25A,V_{DD}=15V V_{GS}=10V	--	23	--	nC
Q_{gs}	Gate to Source Charge		--	8	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	4.5	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	50	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	200	A
V_{SD}	Diode Forward Voltage	I_S=50A,V_{GS}=0V	--	--	1.5	V
t_{rr}	Reverse Recovery Time	I_S=50A,T_j=25°C dI_F/dt=100A/us,V_{GS}=0V	--	30	--	ns
Q_{rr}	Reverse Recovery Charge		--	35	--	nC
Pulse width tp≤380μs,δ≤2%						

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: EAS condition : Tj=25 ,VDD= ℃ 30V,VG=10V,L=0.5mH,Rg=25Ω

a3: I_{SD} =50A,di/dt ≤100A/us,V_{DD}≤$BV_{DS,}$ Start T_J=25℃

Test Circuit and Waveform

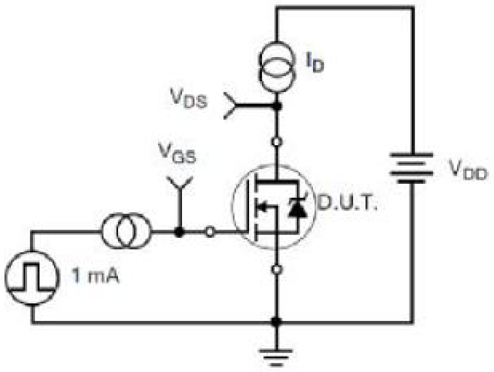


Figure 17. Gate Charge Test Circuit

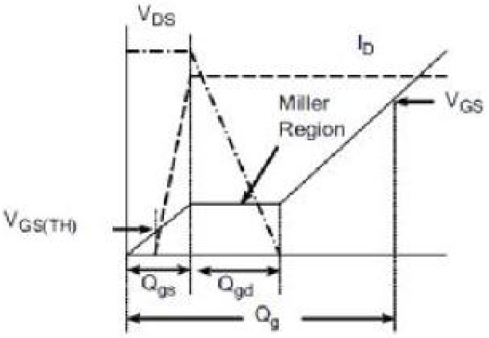


Figure 18. Gate Charge Waveform

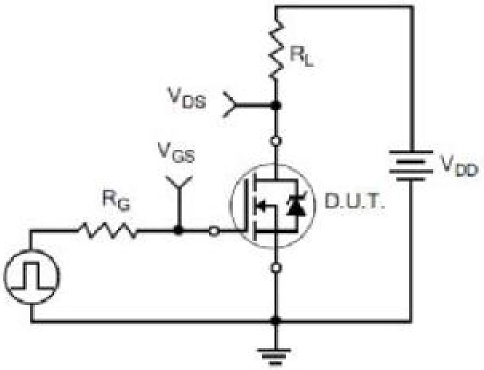


Figure 19. Resistive Switching Test Circuit

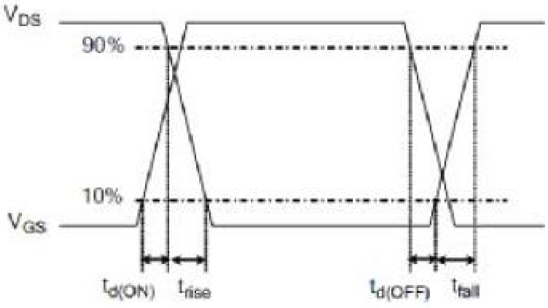


Figure 20. Resistive Switching Waveforms

C

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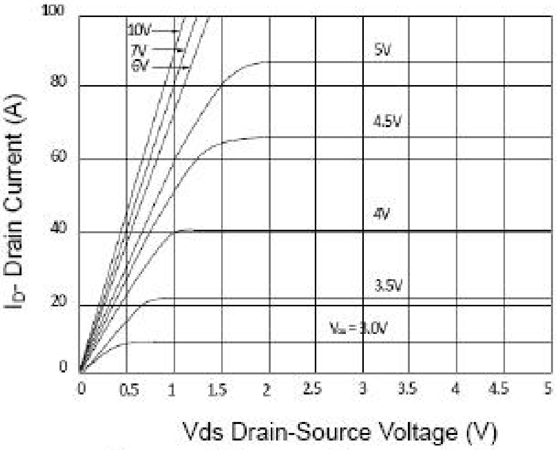


Figure 1 Output Characteristics

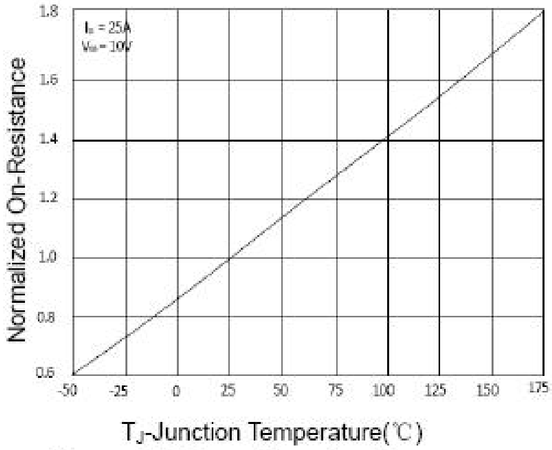


Figure 4 Rdson-JunctionTemperature

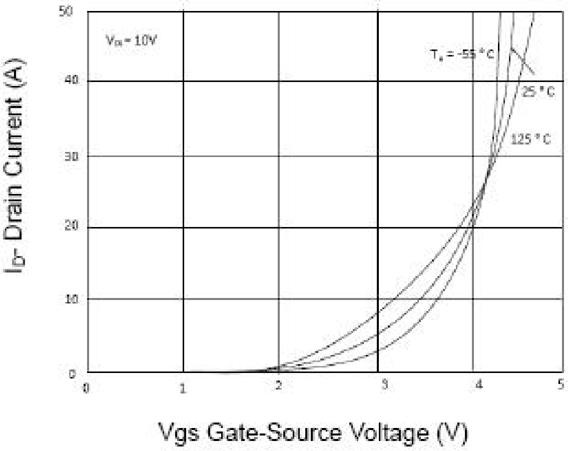


Figure 2 Transfer Characteristics

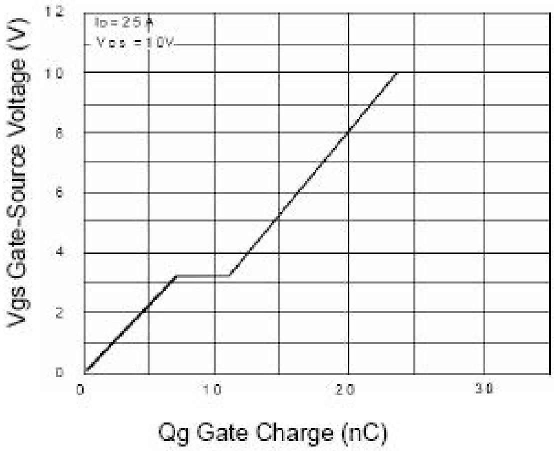


Figure 5 Gate Charge

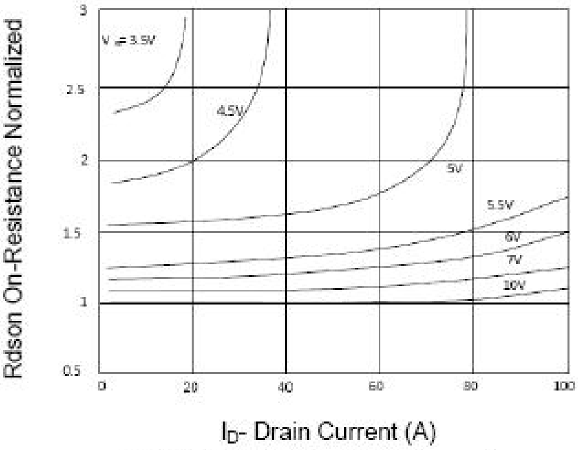


Figure 3 Rdson- Drain Current

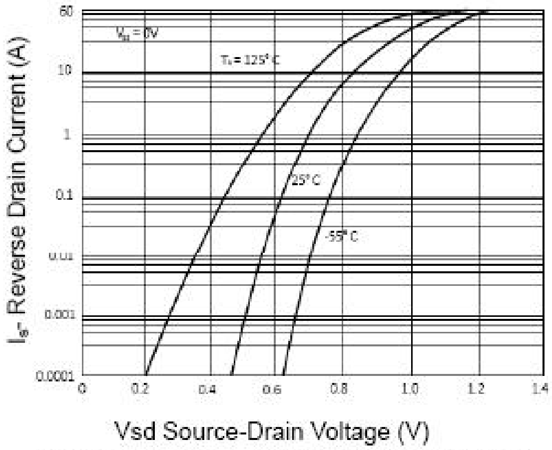
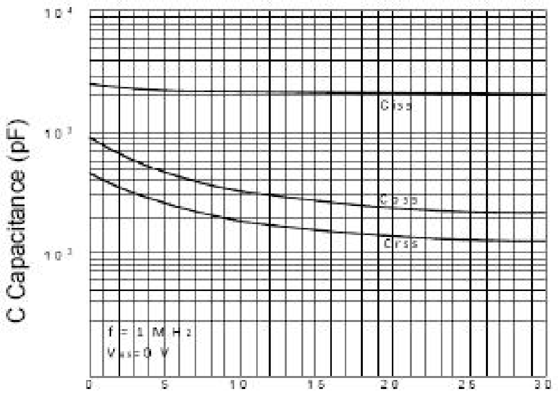
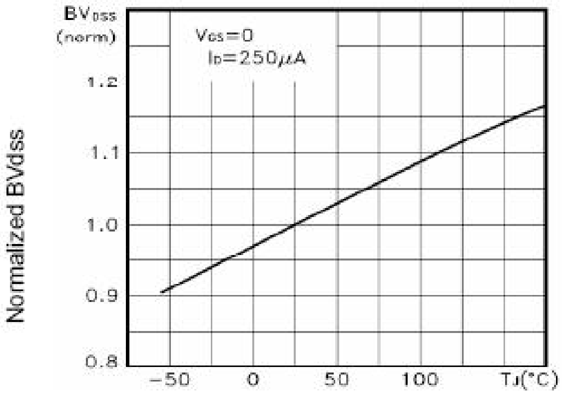


Figure 6 Source- Drain Diode Forward



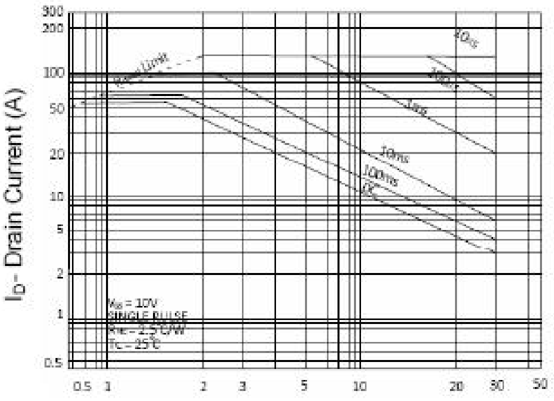
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



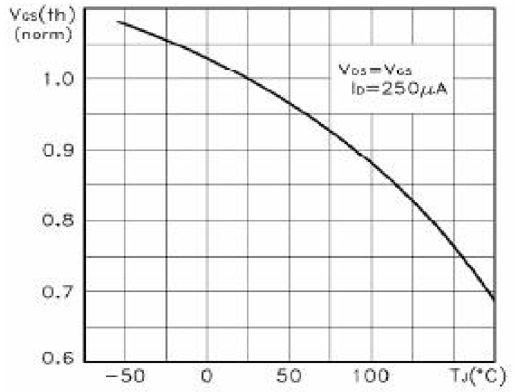
TJ-Junction Temperature(℃)

Figure 9 BV_{DSS} vs Junction Temperature



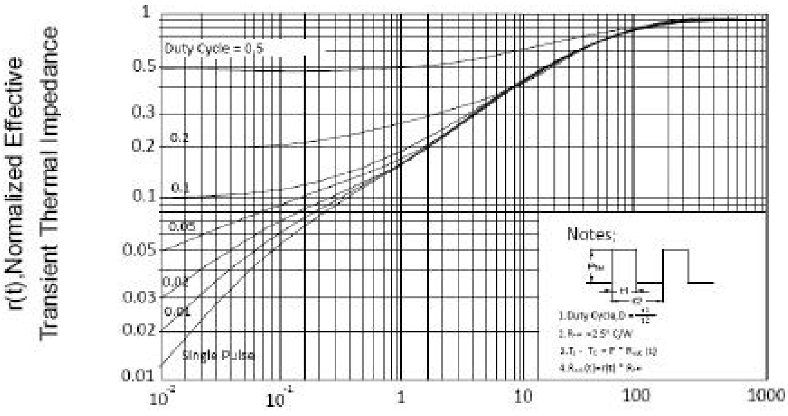
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



TJ-Junction Temperature(℃)

Figure 10 $V_{GS(th)}$ vs Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance